Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Previously Presented) A process for generating a structured component, comprising:

forming a first layer on a substrate,

forming a second layer on the first layer,

generating on the second layer a mask with a first structure and second structure,

performing an isotropic process on the second layer, which transfers the first structure into the second layer, and

after performing the isotropic process, performing an anisotropic process on the first layer, which transfers the second structure into the first layer, wherein the first structure is different from the second structure.

2. (Canceled)

3. (Previously Presented) The process of claim 1, wherein the first structure of the mask is a rough structure and the second structure of the mask is a fine structure, and the smallest expansion of the rough structure is at least twice as large as the smallest expansion of the fine structure.

4. (Previously Presented) The process of claim 1, wherein performing an isotropic process includes using an etching agent which is selective for the second layer.

5. (Previously Presented) The process of claim 1, wherein forming at least one of the first layer or the second layer includes forming a metal layer.

6. (Previously Presented) The process of claim 1, wherein the first layer is a Pt layer and the second layer is an Au layer.

7. (Previously Presented) The process of claim 1, wherein generating on the second layer a mask includes forming a photoresist layer and performing photolithography on the photoresist layer to form the mask.

8. (Previously Presented) The process of claim 1, wherein:

performing the isotropic process removes the second layer below the mask, and

the mask structure is lowered onto the first layer in areas in which the second layer beneath the mask is removed.

9. (Previously Presented) The process of claim 1:

performing an isotropic process includes structuring the second layer with wet chemical isotropic etching, and

performing an anisotropic process includes structuring the first layer with a dry anisotropic etching process.

10. (Previously Presented) The process of claim 1, wherein performing an isotropic process on the second layer removes the second layer entirely except for one or several areas below the mask.

11. (Previously Presented) The process of claim 1, wherein after performing the anisotropic process, the mask is removed.

12. (Previously Presented) The process of claim 1, wherein:

the first layer is formed on functional layers on the substrate,

the first layer and second layer are metal layers,

the first structure of the mask is a geometrically shaped area and the second structure is a linear structure that originates from the first structure,

performing the isotropic process structures the second layer into an area which lies below the geometrically shaped area of the mask and forms a bond pad,

performing the anisotropic process transfers the linear structure of the mask into the first layer, forming a contact line, and

the bond pad has approximately a shape of the first structure and a cross section which widens towards the substrate.

13. (Previously Presented) The process of claim 12, wherein there are multiple linear structures and the linear structures of the mask are in grate arrangements.

14. (Previously Presented) An electrical component formed as a surface wave component, comprising:

a substrate, and

a first layer and a second layer on the substrate, wherein the first layer is different from the second layer, the second layer is structured into a first structure, the first layer is structured into a second structure and the first layer is between the second layer and the substrate;

wherein the first structure in the second layer is structured by an isotropic structuring process, the second structure is structured by an anisotropic structuring process and the first structure is different from the second structure, and

wherein the first layer and the second layer form electrical conductors of the electrical component, the first structure includes a bond pad and the second structure includes contact lines, the contact lines are electrically conducting microstructures and the substrate includes a piezoelectric crystal.

15-17. (Canceled)

18. (Previously Presented) The electrical component of claim 14, wherein the contact lines are formed in a grate pattern.

19. (Previously Presented) The electrical component of claim 14, wherein:

the contact lines include a first electrically conducting metal, and

the bond pad includes the first electrically conducting metal and a second electrically conducting metal.

20. (Previously Presented) The electrical component of claim 19, wherein the first electrically conducting metal is Pt and the second electrically conducting metal is Au.

21-23. (Canceled)

24. (Previously Presented) The process of claim 1 wherein

performing the isotropic process only transfers the first structure into the second layer, and

performing the anisotropic process transfers the second structure into the first layer.

25-27. (Cancelled)

28. (Currently Amended) The process of claim 1, wherein forming the second layer includes forming the second layer of a material that is different ~~that~~ than material of the first layer.

29. (Previously Presented) The process of claim 1, wherein performing the anisotropic process transfers the first structure into the first layer.

30. (Previously Presented) The component of claim 14, wherein the first layer includes the first structure.

31-33. (Cancelled)